# **Unbuffered Inverter**

The MC74VHC1GU04 is an advanced high speed CMOS Unbuffered inverter fabricated with silicon gate CMOS technology. It achieves high speed operation similar to equivalent Bipolar Schottky TTL while maintaining CMOS low power dissipation.

This device consists of a single unbuffered inverter. In combination with others, or in the MC74VHCU04 Hex Unbuffered Inverter, these devices are well suited for use as oscillators, pulse shapers, and in many other applications requiring a high–input impedance amplifier. For digital applications, the MC74VHC1G04 or the MC74VHC04 are recommended.

The internal circuit is composed of three stages, including a buffer output which provides high noise immunity and stable output.

The MC74VHC1GU04 input structure provides protection when voltages up to 7V are applied, regardless of the supply voltage. This allows the MC74VHC1GU04 to be used to interface 5V circuits to 3V circuits.

- High Speed:  $t_{PD} = 2.5 \text{ ns}$  (Typ) at  $V_{CC} = 5 \text{ V}$
- Low Power Dissipation:  $I_{CC} = 2\mu A$  (Max) at  $T_A = 25^{\circ}C$
- Power Down Protection Provided on Inputs
- Balanced Propagation Delays
- Pin and Function Compatible with Other Standard Logic Families
- Latchup Performance Exceeds 300mA

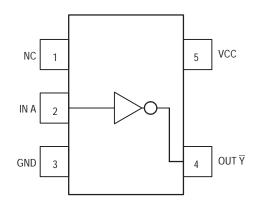


Figure 1. 5-Lead SOT-353 Pinout (Top View)

#### LOGIC SYMBOL





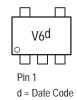
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SC-88A / SOT-353 DF SUFFIX CASE 419A

### MARKING DIAGRAM



PIN ASSIGNMENT							
1	NC						
2	IN A						
3	GND						
4	OUT T						
5	VCC						

#### **ORDERING INFORMATION**

See detailed ordering and shipping information in the package dimensions section on page 4 of this data sheet.

### **FUNCTION TABLE**

Y Output
Н
L

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#### **MAXIMUM RATINGS\***

Characteristics	Symbol	Value	Unit
DC Supply Voltage	V <sub>CC</sub>	-0.5 to +7.0	V
DC Input Voltage	VIN	-0.5 to +7.0	V
DC Output Voltage V <sub>CC</sub> = 0 High or Low State	Vout	−0.5 to 7.0 −0.5 to V <sub>CC</sub> + 0.5	V
Input Diode Current	Iк	-20	mA
Output Diode Current $(V_{OUT} < GND; V_{OUT} > V_{CC})$	IOK	+20	mA
DC Output Current, per Pin	IOUT	+25	mA
DC Supply Current, $V_{CC}$ and GND	ICC	+50	mA
Power dissipation in still air, SC–88A †	PD	200	mW
Lead temperature, 1 mm from case for 10 s	ΤL	260	°C
Storage temperature	T <sub>stg</sub>	-65 to +150	°C

\* Maximum Ratings are those values beyond which damage to the device may occur. Exposure to these conditions or conditions beyond those indicated may adversely affect device reliability. Functional operation under absolute-maximum-rated conditions is not implied. Functional operation should be restricted to the Recommended Operating Conditions.

†Derating — SC--88A Package: -5 mW/°C from 65° to 125°C

### **RECOMMENDED OPERATING CONDITIONS**

Characteristics	Symbol	Min	Max	Unit
DC Supply Voltage	VCC	2.0	5.5	V
DC Input Voltage	VIN	0.0	5.5	V
DC Output Voltage	VOUT	0.0	VCC	V
Operating Temperature Range	TA	-55	+85	°C
Input Rise and Fall Time $V_{CC} = 3.3V \pm 0.3V$ $V_{CC} = 5.0V \pm 0.5V$	t <sub>r</sub> , t <sub>f</sub>	0 0	No Limit No Limit	ns/V

			Vcc	т	T <sub>A</sub> = 25°C		T <sub>A</sub> ≤	85°C	T <sub>A</sub> ≤ 125°C			
Symbol	Parameter	Test Conditions	(V)	Min	Тур	Мах	Min	Мах	Min	Max	Unit	
VIH	Minimum High–Level Input Voltage		2.0 3.0 4.5 5.5	1.7 2.4 3.6 4.4			1.7 2.4 3.6 4.4		1.7 2.4 3.6 4.4		V	
VIL	Maximum Low–Level Input Voltage		2.0 3.0 4.5 5.5			0.3 0.6 0.9 1.1		0.3 0.6 0.9 1.1		0.3 0.6 0.9 1.1	V	
VOH	Minimum High–Level Output Voltage V <sub>IN</sub> = V <sub>IH</sub> or V <sub>IL</sub>	VIN = VIH or VIL IOH = -50µA	2.0 3.0 4.5	1.9 2.9 4.4	2.0 3.0 4.5		1.9 2.9 4.4		1.9 2.9 4.4		V	
		$V_{IN} = V_{IH} \text{ or } V_{IL}$ $I_{OH} = -4mA$ $I_{OH} = -8mA$	3.0 4.5	2.58 3.94			2.48 3.80		2.34 3.66		V	
V <sub>OL</sub>	Maximum Low–Level Output Voltage VIN = VIH or VIL	VIN = VIH or VIL IOL = 50µA	2.0 3.0 4.5		0.0 0.0 0.0	0.1 0.1 0.1		0.1 0.1 0.1		0.1 0.1 0.1	V	
		V <sub>IN</sub> = V <sub>IH</sub> or V <sub>IL</sub> I <sub>OL</sub> = 4mA I <sub>OL</sub> = 8mA	3.0 4.5			0.36 0.36		0.44 0.44		0.52 0.52	V	
I <sub>IN</sub>	Maximum Input Leakage Current	$V_{IN} = 5.5V \text{ or GND}$	0 to 5.5			±0.1		±1.0		±1.0	μA	
ICC	Maximum Quiescent Supply Current	$V_{IN} = V_{CC}$ or GND	5.5			2.0		20		40	μA	

### DC ELECTRICAL CHARACTERISTICS

### AC ELECTRICAL CHARACTERISTICS ( $C_{load} = 50 \text{ pF}$ , Input $t_r = t_f = 3.0 \text{ns}$ )

				T <sub>A</sub> = 25°C		C	T <sub>A</sub> ≤	85°C	°C T <sub>A</sub> ≤ 125°C			
Symbol	Parameter	Test Condi	tions	Min	Тур	Max	Min	Max	Min	Мах	Unit	
tPLH, Maximum tPHL Propogation Delay, Input A to Y	$V_{CC} = 3.0 \pm 0.3 V$	C <sub>L</sub> = 15 pF C <sub>L</sub> = 50 pF		3.5 4.8	8.9 11.4		10.5 13.0		12.0 15.5	ns		
	Input A to Y	$V_{CC} = 5.0 \pm 0.5 V$	C <sub>L</sub> = 15 pF C <sub>L</sub> = 50 pF		2.5 3.8	5.5 7.0		6.5 8.0		8.0 9.5		
C <sub>IN</sub>	Maximum Input Capacitance				4	10		10		10	pF	
Typical @ 25°C, V <sub>CC</sub> = 5.0V										DV V		
Срп	Power Dissipation Car	pacitance (Note 1.)						22			рF	

 
 CPD
 Power Dissipation Capacitance (Note 1.)
 22
 pF

 1. CPD is defined as the value of the internal equivalent capacitance which is calculated from the operating current consumption without load. Average operating current can be obtained by the equation: I<sub>CC(OPR)</sub>=CPD • V<sub>CC</sub> • f<sub>in</sub>+I<sub>CC</sub>. CPD is used to determine the no-load dynamic power consumption; PD = CPD • V<sub>CC</sub><sup>2</sup> • f<sub>in</sub> + I<sub>CC</sub> • V<sub>CC</sub>.

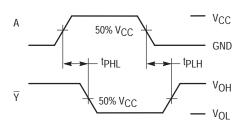
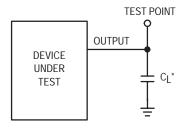


Figure 2. Switching Waveforms



\*Includes all probe and jig capacitance

#### Figure 3. Test Circuit

### **DEVICE ORDERING INFORMATION**

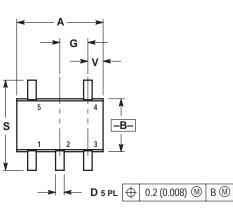
Device Order Number	Circuit Indicator	Temp Range Identifier	Technology	Device Function	Package Suffix	Tape & Reel Suffix	Package Type	Tape and Reel Size
MC74VHC1GU04DFT1	MC	74	VHC1G	U04	DF	T1	SC-88A / SOT-353	7–Inch/3000 Unit

### PACKAGE DIMENSIONS

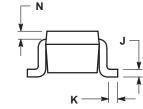
SC-88A / SOT-353 DF SUFFIX 5-LEAD PACKAGE CASE 419A-01 **ISSUE B** 

NOTES: 1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982. 2. CONTROLLING DIMENSION: MM.

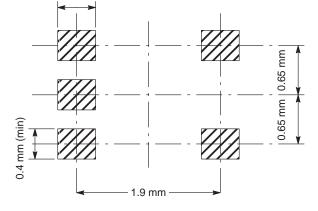
	INC	HES	MILLIN	IETERS	
DIM	MIN	MAX	MIN	MAX	
Α	0.071	0.087	1.80	2.20	
В	0.045	0.053	1.15	1.35	
С	0.031	0.043	0.80	1.10	
D	0.004	0.012	0.10	0.30	
G	0.026	BSC	0.65 BSC		
Н		0.004		0.10	
J	0.004	0.010	0.10	0.25	
К	0.004	0.012	0.10	0.30	
Ν	0.008 REF		0.20	REF	
S	0.079	0.087	2.00	2.20	
V	0.012	0.016	0.30	0.40	



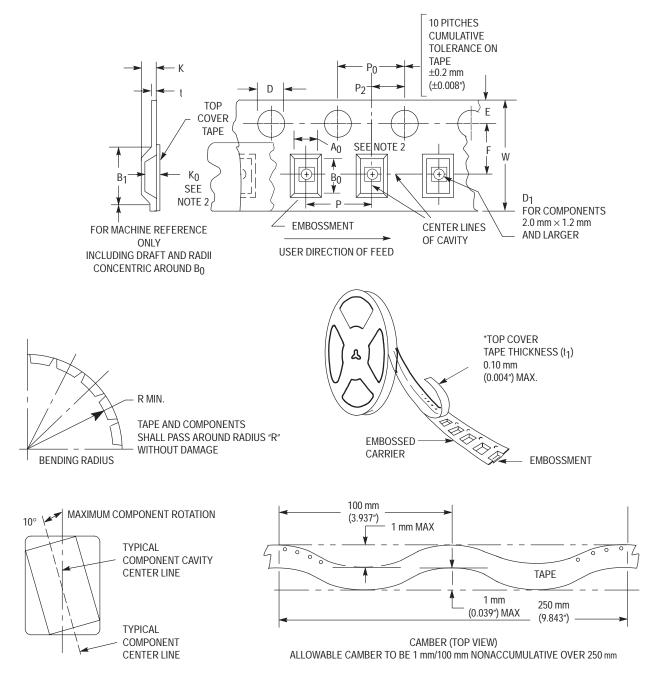
C



0.5 mm (min)



н





Tape Size	B <sub>1</sub> Max	D	D <sub>1</sub>	Е	F	к	Р	P <sub>0</sub>	P <sub>2</sub>	R	т	w
8 mm	4.35 mm (0.171″)	1.5 +0.1/ -0.0 mm (0.059 +0.004/ -0.0")	1.0 mm Min (0.039″)	1.75 ±0.1 mm (0.069 ±0.004")	3.5 ±0.5 mm (1.38 ±0.002")	2.4 mm (0.094")	4.0 ±0.10 mm (0.157 ±0.004")	4.0 ±0.1 mm (0.156 ±0.004")	2.0 ±0.1 mm (0.079 ±0.002")	25 mm (0.98″)	0.3 ±0.05 mm (0.01 +0.0038/ -0.0002")	8.0 ±0.3 mm (0.315 ±0.012")

EMBOSSED CARRIER DIMENSIONS (See Notes 1 and 2)

Metric Dimensions Govern–English are in parentheses for reference only.
 A<sub>0</sub>, B<sub>0</sub>, and K<sub>0</sub> are determined by component size. The clearance between the components and the cavity must be within 0.05 mm min to 0.50 mm max. The component cannot rotate more than 10° within the determined cavity

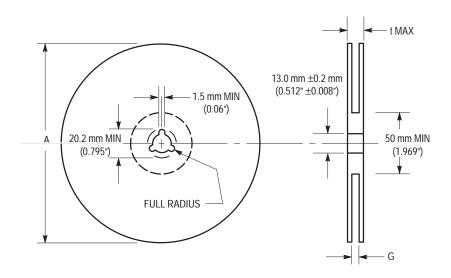


Figure 5. Reel Dimensions

#### **REEL DIMENSIONS**

Tape Size	A Max	G	t Max
8 mm	330 mm	8.400 mm, +1.5 mm, -0.0	14.4 mm
	(13")	(0.33", +0.059", -0.00)	(0.56″)

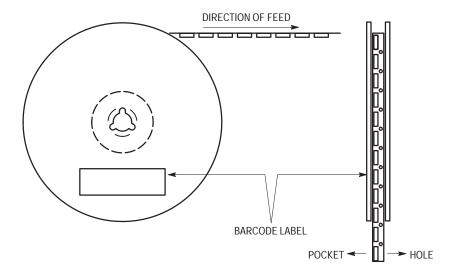
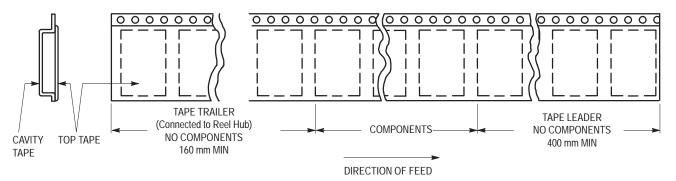
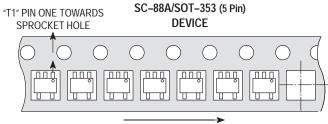


Figure 6. Reel Winding Direction







User Direction of Feed

Figure 8. Reel Configuration

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